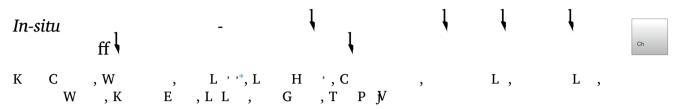


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journal homepage: www.elsevier.com/locate/compositesa



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ABSTRACT

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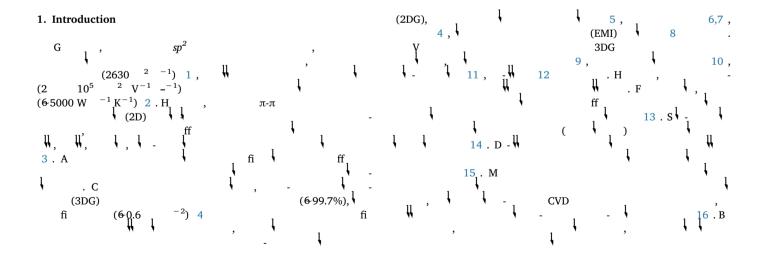
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(3DG) . H (3D) (SLM) in-situ (CVD) С 3DG CVD SLM ff (. T 3DG/ ff 88% (EMI) EMI ffi-

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32.3 B



47.8 B

2.7 GH

SLM

*C : G \ I , C U G , W 430074, PR C .

E-mail address: \ @ . . (.L).

:// . /10.1016/ \frak{N} .2020.105904 R 31 J 2020; R 1 A $\frak{1}$ 2020; A 13 A $\frak{1}$ 2020

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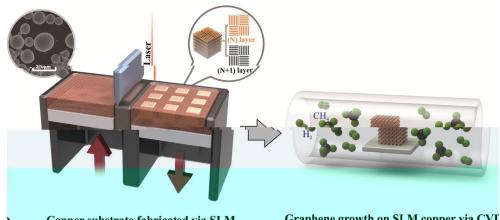
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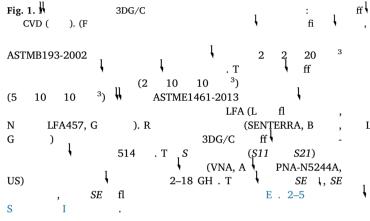
Copper substrate fabricated via SLM

Graphene growth on SLM copper via CVI

in-situ

SLM (

Excessive melting



3. Results and discussion

3.1. Formation of SLM copper

Weak sintering

(a)

3.1.1. SLM manufacturing of copper under different line energy densities T . Dff

Unstable melting

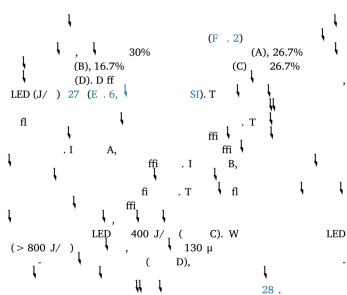
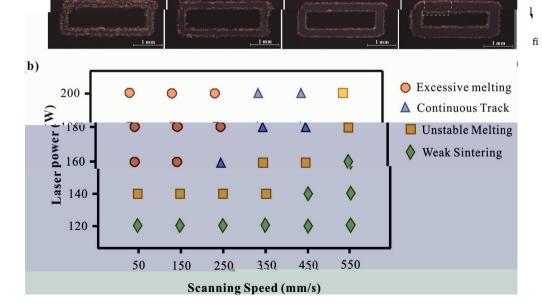


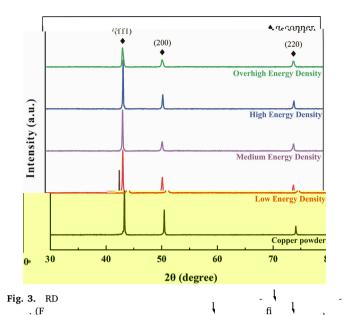
Fig. 2. () T

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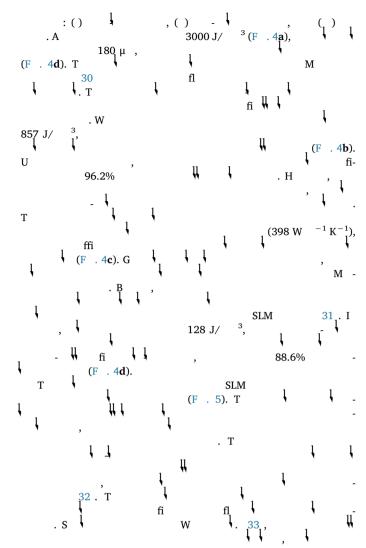
Continuous track



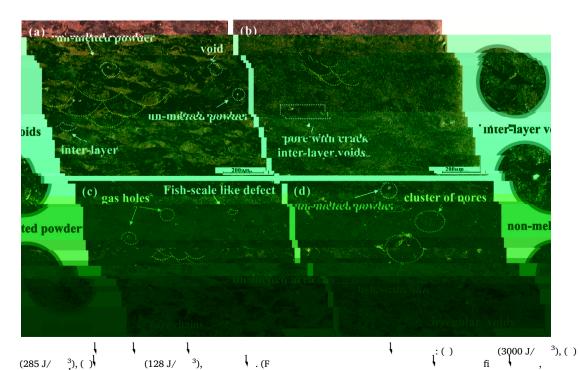
3.1.2. Formation of anisotropic microstructure under different volumetric

energy density ₩ _{RD} T $2\theta = 43.32$ $(1\ 1\ 1)$ (2 0 0) fl ff (F . 3), $(1\ 1\ 1)$ RD ff fi SLM SLM ffff 29 . $\boldsymbol{\iota}^T$ SLM . T

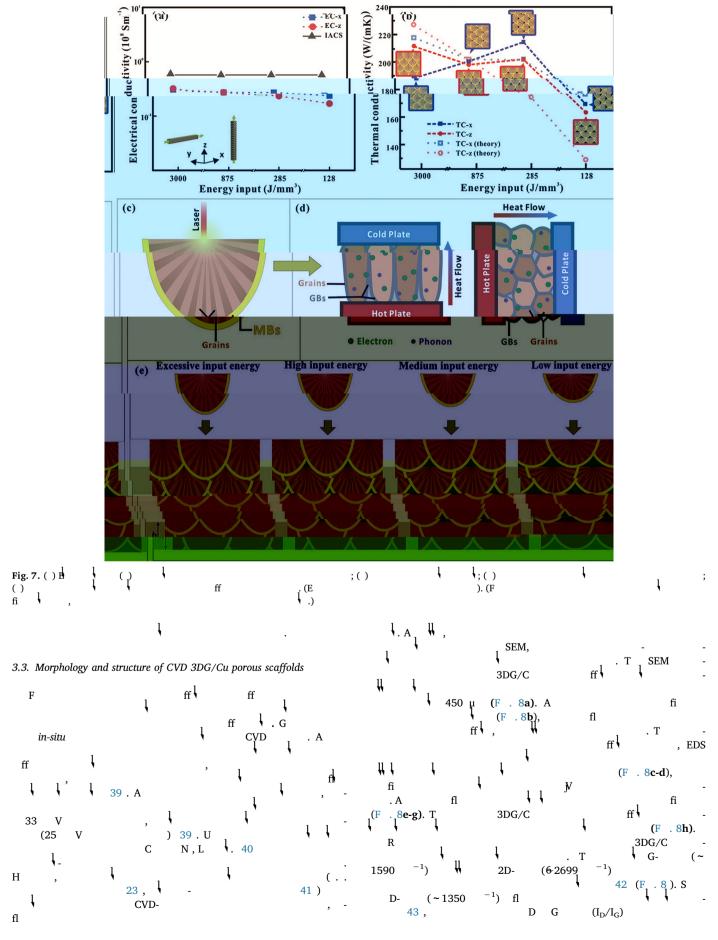
Fig. 4. O ³), ()



(857 J/



K. Cheng, et al. Composites Part A 135 (2020) 105904



K. Cheng, et al. Composites Part A 135 (2020) 105904

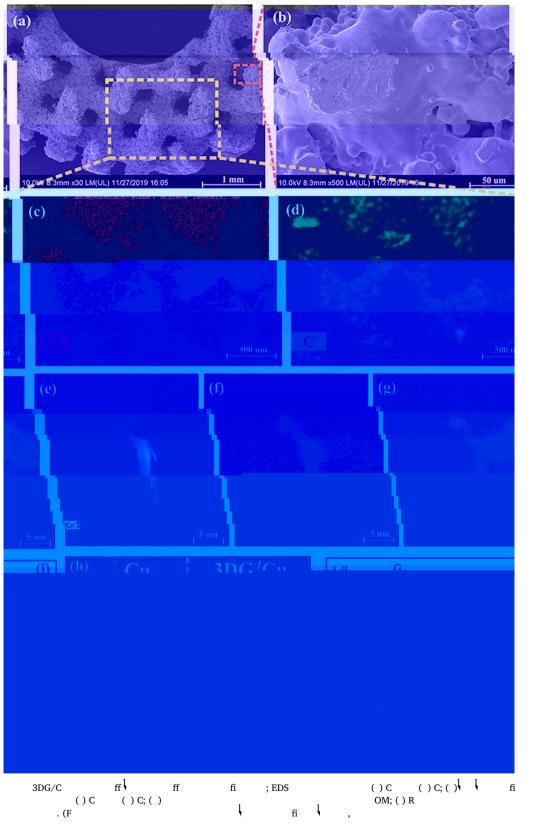
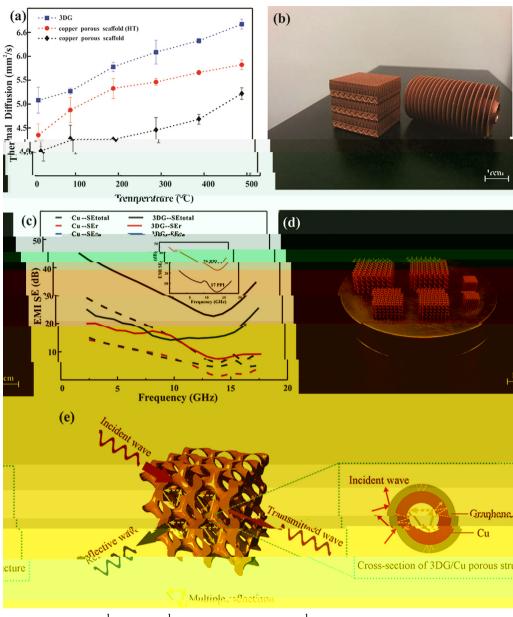


Fig. 8. (-) SEM 3DG/C ff f fi fi ; EDS () C () C; () fi SEM ff fi ; EDS () C () C; () fi SEM ff (()

K. Cheng, et al. Composites Part A 135 (2020) 105904



 $\operatorname{ff}^{\text{l}}:(\)$ Fig. 9, P 3DG/C ff ; () SLM fl fl ff \ ; () EMI SE; () C ff ; () S 3DG/C EMI. (F fi

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C Coating materials Substrate Method Maximum shielding Improvement of thermal Ref efficiency (dB) property (%) G G 37 50 11 G G 29.3 PS 56 PMMA 19 57 C /G G G G ţ ţ /C fi 8.5 58 N 554 59 CVD C -N 20 60 2.4 С 61 С 47 6.3 62

EMI

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1 Note:)-PPMA, -PS.

CVD + SLM

С

Table 1

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K. Cheng, et al. Composites Part A 135 (2020) 105904

HT (F . 9a). S F . 9e. W SE_r SE_a , in-situ 3DG/C 3DG/C ff \ fl ff . s НТ 3DG/C 1-2 fl . I . T EM EM SLM SE_r . O 500 μ) (F . 9b),EM ff 54 . I 1). I fl . M 3DG/C ff EM EMI, EMI SE, EM . T (EM) 2-18 GH (F . 9c), 3D . W in-situ EM ↓ . I SE 15.9 32.3 B, CVD 47.8 B (88.2%), 3.3 6-20 B. T 3DG/C . J K EMI 55 . I . T EMI SE 133%) 20 110 PPI (3DG/C). R **J**V K 45 ↓ EMI ff \ . W 17 26 PPI (F . 9c insert) 105% EMI *ŞE*. I ff \ SLM. T 4. Conclusions 26 PPI 3DG/C EMI SE 3DG/C in-situ ff \ ^{32.3} B, ↓ 99.9% EMI . T CVD 60 ff () 46 . T EMI (30 ff 3DG/C $_{\rm T}$ \downarrow 1. I EMI SE 3DG/C 3DG/C EMI SE 3D 15.9 (32.3 B, 47.8 B (88.2% 26.8%), 3DG/C Т EMI (SE_r) , ff . T (SE_a) fl (EM) 47, fl . T **EMI** 3ĎG/C **EMI** Credit authorship contribution statement ЕM Kaka Cheng: C . Wei Xiong: V 50 . R **EMI** . Yan Li: W - & . Liang Hao: F . Chunze Yan:
. Zhaoqing Li: V . Zhufeng Liu:
. Yushen Wang: I , S . Khamis Essa:
& . Li Lee: D . Xin Gong: S .
. & , S . , S . Liang Hao: F C 51.F 52 S O₂ 53 . W ff↓ 3DG/C Ton Peijs: W

Declaration of Competing Interest

Acknowledgement

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Appendix A. Supplementary data

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L 2010;10(9):3512-6.

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   2020;161:479-85.
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M L 2017;200:97–100.
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                                     P A 2018;12:475–84.
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